



501.39474X00

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): H. NAKANO, et al  
Serial No.: 09/760,704  
Filed: January 17, 2001  
For: METHOD OF PROCESSING A SEMICONDUCTOR DEVICE  
Group: 2812  
Examiner:

PRELIMINARY AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

July 31, 2001

Sir:

The following preliminary amendments and remarks are respectfully submitted in connection with the above-identified application.

IN THE SPECIFICATION:

Please replace the original specification with the attached Substitute Specification.

IN THE ABSTRACT OF THE DISCLOSURE:

Please amend the abstract as follows:

ABSTRACT OF THE DISCLOSURE

A method of processing a semiconductor device includes the steps of generating plasma in a processing chamber to form a thin film on a semiconductor device or to process a thin